



HVGT high voltage silicon rectifier diodes is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

**SHAPE DISPLAY:**



**FEATURES:**

1. High reliability design.
2. High voltage design.
3. High frequency .
4. Conform to RoHS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.
6. Ultra-Fast Recovery.

**APPLICATIONS:**

1. High voltage multiplier circuit
2. Electrostatic generator circuit .
3. General purpose high voltage rectifier.
4. Medical X-ray machine HV power supply.

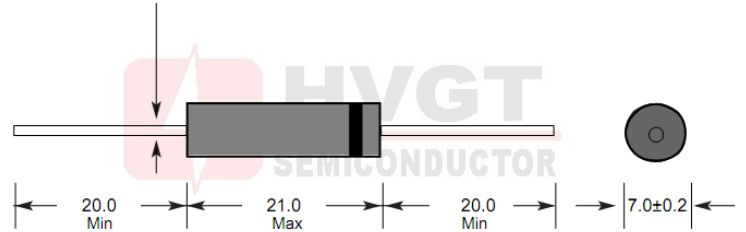
**MECHANICAL DATA:**

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 2.1 grams (approx).

**SIZE: (Unit:mm)**

**HVGT NAME: DO-721**

**DO-721 Series**  
Lead Diameter 1.2mm



Unit:mm

**MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)**

| Items                                | Symbols   | Condition                         | Data Value | Units       |
|--------------------------------------|-----------|-----------------------------------|------------|-------------|
| Repetitive Peak Rense Voltage        | $V_{RRM}$ | $T_a=25^{\circ}C;$                | 15         | kV          |
| Average Output Current               | $I_F$     | $T_a=55^{\circ}C;$ Resistive Load | 500        | mA          |
| Suege Current                        | $I_{FSM}$ | $T_a=25^{\circ}C;$ 1/2 Sine(60Hz) | 20         | A           |
| Junction Temperature                 | $T_J$     |                                   | -55~+150   | $^{\circ}C$ |
| Allowable Operation Case Temperature | $T_c$     |                                   | 125        | $^{\circ}C$ |
| Storage Temperature                  | $T_{STG}$ |                                   | -55~+150   | $^{\circ}C$ |

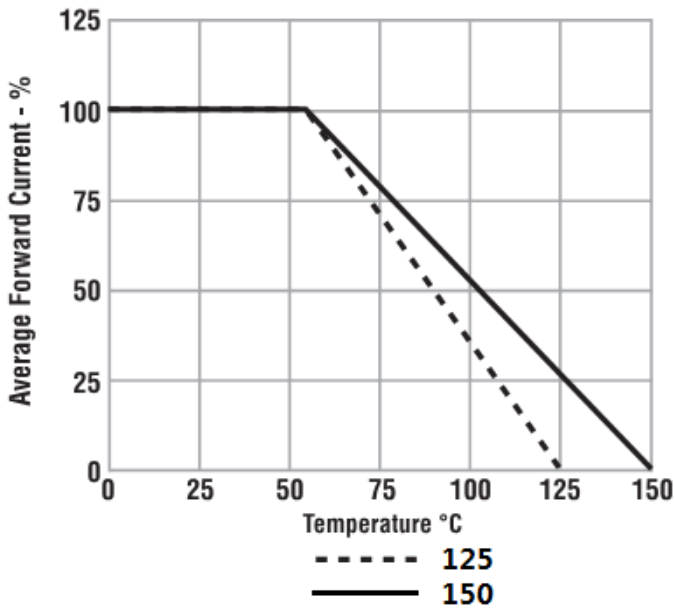
**ELECTRICAL CHARACTERISTICS:  $T_a=25^{\circ}C$  (Unless otherwise specified)**

| Items                         | Symbols  | Condition  | Data value | Units   |
|-------------------------------|----------|--|------------|---------|
| Maximum Forward Voltage Drop  | $V_F$    | at $25^{\circ}C;$ $I_F = I_{F(AV)}$                              | 16         | V       |
| Maximum Reverse Current       | $I_{R1}$ | at $25^{\circ}C;$ $V_R = V_{RRM}$                                | 0.5        | $\mu A$ |
|                               | $I_{R2}$ | at $125^{\circ}C;$ $V_R = V_{RRM}$                               | 50         | $\mu A$ |
| Maximum Reverse Recovery Time | $T_{RR}$ | at $25^{\circ}C;$ $I_F=0.5I_R;$ $I_R=I_{FAVM};$ $I_{RR}=0.25I_R$ | 50         | nS      |
| Junction Capacitance          | $C_J$    | at $25^{\circ}C;$ $V_R=0V;$ $f=1MHz$                             | 3.5        | pF      |



**Fig 1**

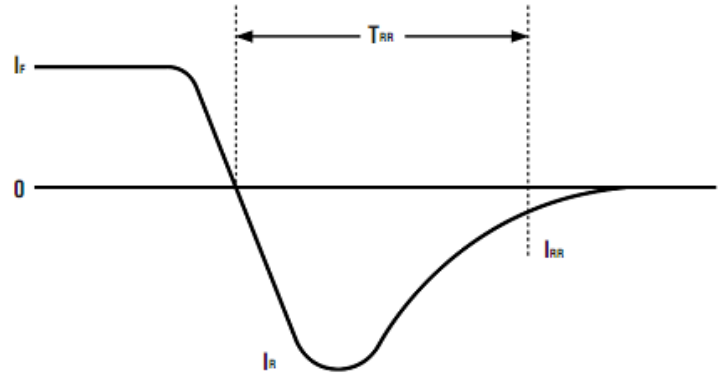
**Forward Current Derating Curve**



Show average current rating at 55°C, unless otherwise specified.  
Max operating temperature is 150°C, unless otherwise specified.

**Fig 2**

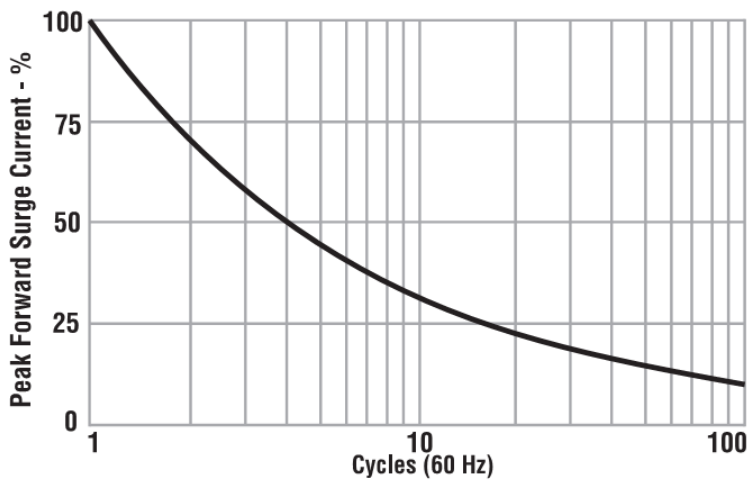
**Reverse Recovery Measurement Waveform**



Typical data capture points:  $I_F = 0.5I_R$ ,  $I_R, I_{RR} = 0.25I_R$   
 $I_R$  is typically the rated average forward current maximum ( $I_{FAVM}$ ) of the D.U.T

**Fig 3**

**Repetitive Surge Current Derating Curve**



This curve represents the percentage of published maximum surge rating as a function of surge repetition.

**Fig 4**

**Reverse Characteristics**

